



TLHG / O / P / R / Y440.

Vishay Semiconductors

High Efficiency LED in \varnothing 3 mm Tinted Diffused Package

Description

The TLH.44.. series was developed for standard applications like general indicating and lighting purposes.

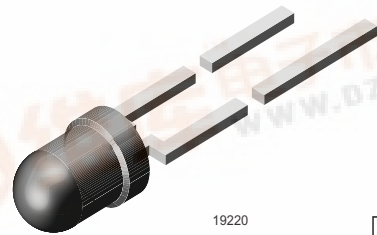
It is housed in a 3 mm tinted diffused plastic package. The wide viewing angle of these devices provides a high on-off contrast.

Several selection types with different luminous intensities are offered. All LEDs are categorized in luminous intensity groups. The green and yellow LEDs are categorized additionally in wavelength groups.

That allows users to assemble LEDs with uniform appearance.

Features

- Standard T-1 package
- Small mechanical tolerances
- Suitable for DC and high peak current
- Wide viewing angle
- Luminous intensity categorized
- Yellow and green color categorized
- Lead-free device



19220



Applications

- Status lights
- OFF / ON indicator
- Background illumination
- Readout lights
- Maintenance lights
- Legend light

Parts Table

Part	Color, Luminous Intensity	Angle of Half Intensity ($\pm\phi$)	Technology
TLHR4400	Red, $I_V > 1.6$ mcd	30 °	GaAsP on GaP
TLHR4401	Red, $I_V > 2.5$ mcd	30 °	GaAsP on GaP
TLHR4405	Red, $I_V > 6.3$ mcd	30 °	GaAsP on GaP
TLHO4400	Soft orange, $I_V > 1.6$ mcd	30 °	GaAsP on GaP
TLHY4400	Yellow, $I_V > 1.6$ mcd	30 °	GaAsP on GaP
TLHY4401	Yellow, $I_V > 2.5$ mcd	30 °	GaAsP on GaP
TLHY4405	Yellow, $I_V > 6.3$ mcd	30 °	GaAsP on GaP
TLHG4400	Green, $I_V > 2.5$ mcd	30 °	GaP on GaP
TLHG4401	Green, $I_V > 4$ mcd	30 °	GaP on GaP
TLHG4405	Green, $I_V > 6.3$ mcd	30 °	GaP on GaP
TLHP4400	Pure green, $I_V > 0.63$ mcd	30 °	GaP on GaP
TLHP4401	Pure green, $I_V > 1$ mcd	30 °	GaP on GaP
TLHP4405	Pure green, $I_V > 1.6$ mcd	30 °	GaP on GaP



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Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

TLHR44.., TLHO44.., TLHY44.., TLHG44.., TLHP44..,

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V _R	6	V
DC Forward current		I _F	30	mA
Surge forward current	t _p ≤ 10 μs	I _{FSM}	1	A
Power dissipation	T _{amb} ≤ 60 °C	P _V	100	mW
Junction temperature		T _j	100	°C
Operating temperature range		T _{amb}	- 40 to + 100	°C
Storage temperature range		T _{stg}	- 55 to + 100	°C
Soldering temperature	t ≤ 5 s, 2 mm from body	T _{sd}	260	°C
Thermal resistance junction/ ambient		R _{thJA}	400	K/W

Optical and Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Red

TLHR44..

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Luminous intensity ¹⁾	I _F = 10 mA	TLHR4400	I _V	1.6	3		mcd
		TLHR4401	I _V	2.5	5		mcd
		TLHR4405	I _V	6.3	10		mcd
Dominant wavelength	I _F = 10 mA		λ _d	612		625	nm
Peak wavelength	I _F = 10 mA		λ _p		635		nm
Angle of half intensity	I _F = 10 mA		φ		± 30		deg
Forward voltage	I _F = 20 mA		V _F		2	3	V
Reverse voltage	I _R = 10 μA		V _R	6	15		V
Junction capacitance	V _R = 0, f = 1 MHz		C _j		50		pF

¹⁾ in one Packing Unit I_{Vmin}/I_{Vmax} ≤ 0.5

Soft Orange

TLHO44..

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Luminous intensity ¹⁾	I _F = 10 mA	TLHO4400	I _V	1.6	4		mcd
Dominant wavelength	I _F = 10 mA		λ _d	598		611	nm
Peak wavelength	I _F = 10 mA		λ _p		605		nm
Angle of half intensity	I _F = 10 mA		φ		± 30		deg
Forward voltage	I _F = 20 mA		V _F		2.4	3	V
Reverse voltage	I _R = 10 μA		V _R	6	15		V
Junction capacitance	V _R = 0, f = 1 MHz		C _j		15		pF

¹⁾ in one Packing Unit I_{Vmin}/I_{Vmax} ≤ 0.5



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Yellow

TLHY44..

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Luminous intensity ¹⁾	$I_F = 10 \text{ mA}$	TLHY4400	I_V	1.6	3		mcd
		TLHY4401	I_V	2.5	5		mcd
		TLHY4405	I_V	6.3	10		mcd
Dominant wavelength	$I_F = 10 \text{ mA}$		λ_d	581		594	nm
Peak wavelength	$I_F = 10 \text{ mA}$		λ_p		585		nm
Angle of half intensity	$I_F = 10 \text{ mA}$		ϕ		± 30		deg
Forward voltage	$I_F = 20 \text{ mA}$		V_F		2.4	3	V
Reverse voltage	$I_R = 10 \mu\text{A}$		V_R	6	15		V
Junction capacitance	$V_R = 0, f = 1 \text{ MHz}$		C_j		50		pF

¹⁾ in one Packing Unit $I_{Vmin}/I_{Vmax} \leq 0.5$

Green

TLHG44..

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Luminous intensity ¹⁾	$I_F = 10 \text{ mA}$	TLHG4400	I_V	2.5	4		mcd
		TLHG4401	I_V	4	6		mcd
		TLHG4405	I_V	6.3	12		mcd
Dominant wavelength	$I_F = 10 \text{ mA}$		λ_d	562		575	nm
Peak wavelength	$I_F = 10 \text{ mA}$		λ_p		565		nm
Angle of half intensity	$I_F = 10 \text{ mA}$		ϕ		± 30		deg
Forward voltage	$I_F = 20 \text{ mA}$		V_F		2.4	3	V
Reverse voltage	$I_R = 10 \mu\text{A}$		V_R	6	15		V
Junction capacitance	$V_R = 0, f = 1 \text{ MHz}$		C_j		50		pF

¹⁾ in one Packing Unit $I_{Vmin}/I_{Vmax} \leq 0.5$

Pure green

TLHP44..

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Luminous intensity ¹⁾	$I_F = 10 \text{ mA}$	TLHP4400	I_V	0.63	2		mcd
		TLHP4401	I_V	1	3		mcd
		TLHP4405	I_V	1.6	3.5		mcd
Dominant wavelength	$I_F = 10 \text{ mA}$		λ_d	555		565	nm
Peak wavelength	$I_F = 10 \text{ mA}$		λ_p		555		nm
Angle of half intensity	$I_F = 10 \text{ mA}$		ϕ		± 30		deg
Forward voltage	$I_F = 20 \text{ mA}$		V_F		2.4	3	V
Reverse voltage	$I_R = 10 \mu\text{A}$		V_R	6	15		V
Junction capacitance	$V_R = 0, f = 1 \text{ MHz}$		C_j		50		pF

¹⁾ in one Packing Unit $I_{Vmin}/I_{Vmax} \leq 0.5$

Typical Characteristics ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

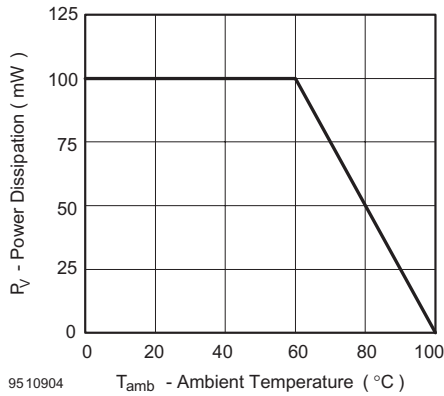


Figure 1. Power Dissipation vs. Ambient Temperature

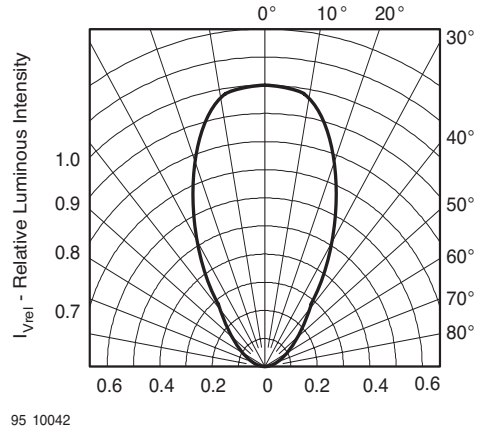


Figure 4. Rel. Luminous Intensity vs. Angular Displacement

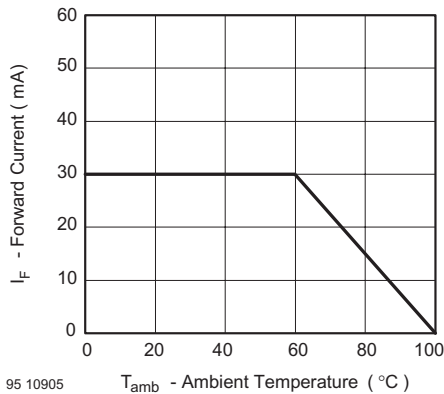


Figure 2. Forward Current vs. Ambient Temperature for InGaN

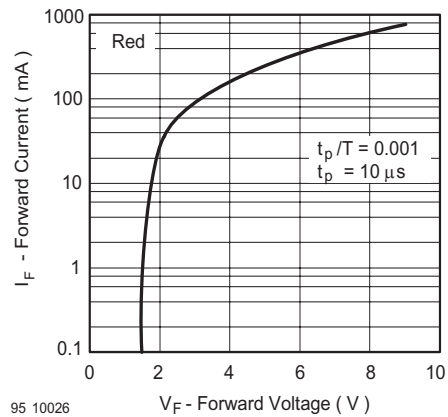


Figure 5. Forward Current vs. Forward Voltage

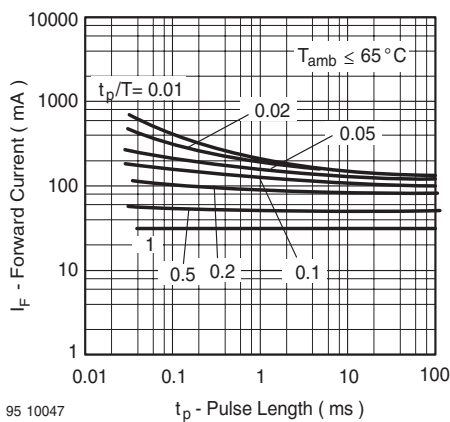


Figure 3. Forward Current vs. Pulse Length

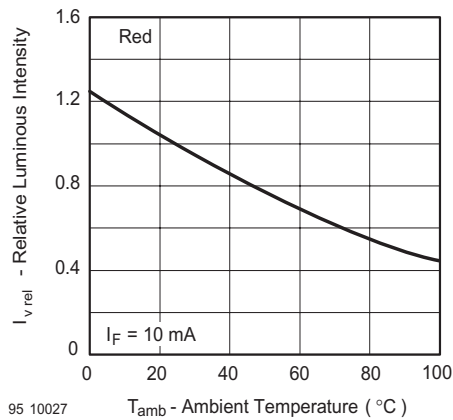


Figure 6. Rel. Luminous Intensity vs. Ambient Temperature



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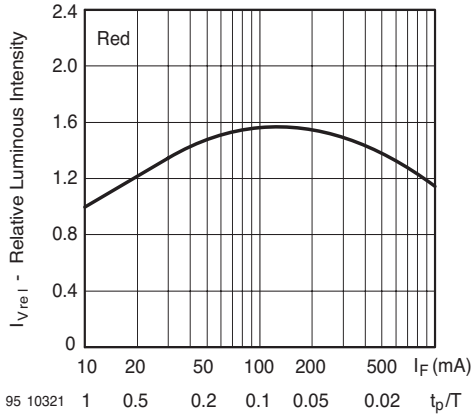


Figure 7. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

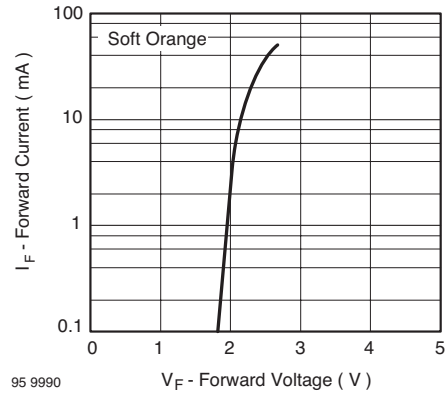


Figure 10. Forward Current vs. Forward Voltage

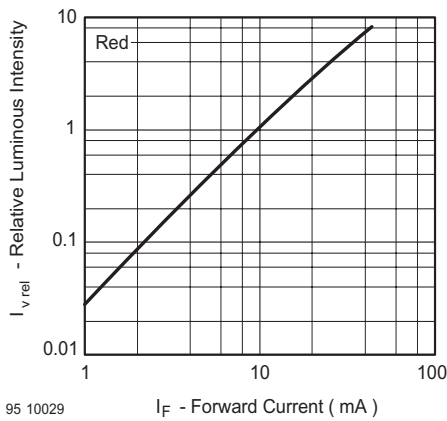


Figure 8. Relative Luminous Intensity vs. Forward Current

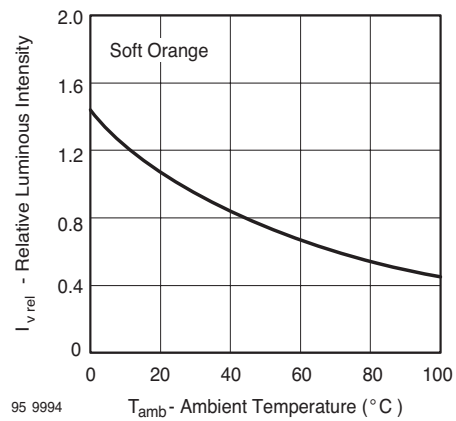


Figure 11. Rel. Luminous Intensity vs. Ambient Temperature

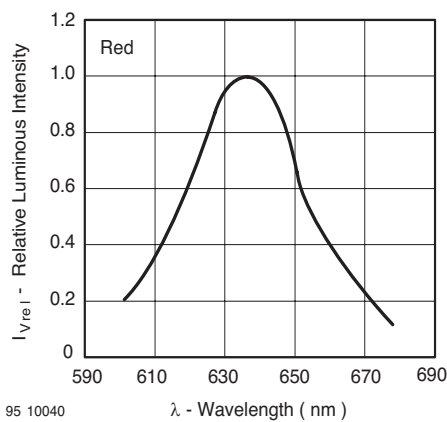


Figure 9. Relative Intensity vs. Wavelength

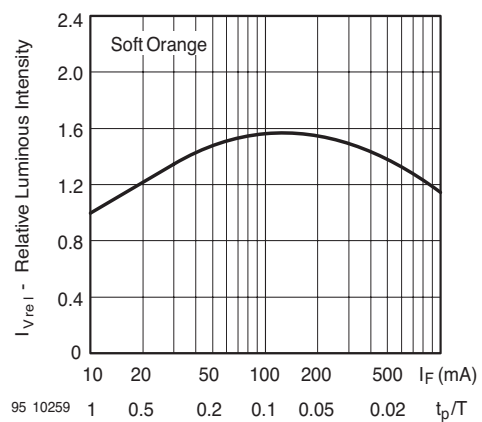


Figure 12. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

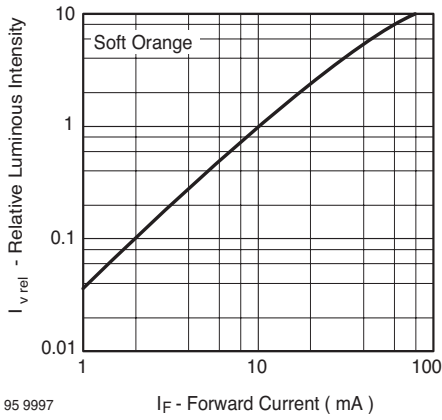


Figure 13. Relative Luminous Intensity vs. Forward Current

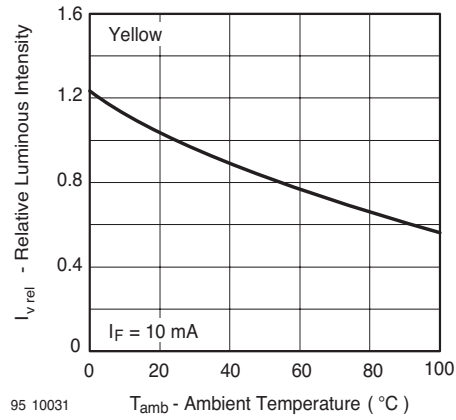


Figure 16. Rel. Luminous Intensity vs. Ambient Temperature

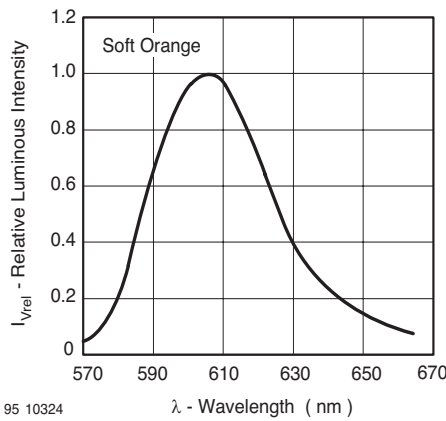


Figure 14. Relative Intensity vs. Wavelength

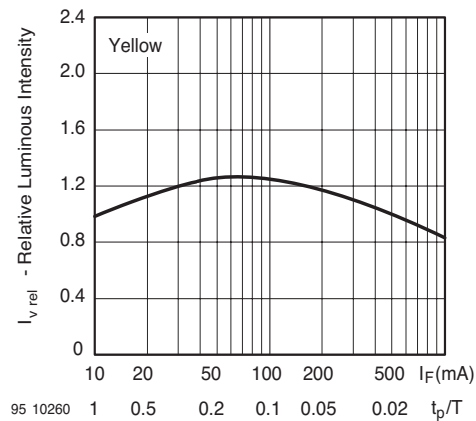


Figure 17. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

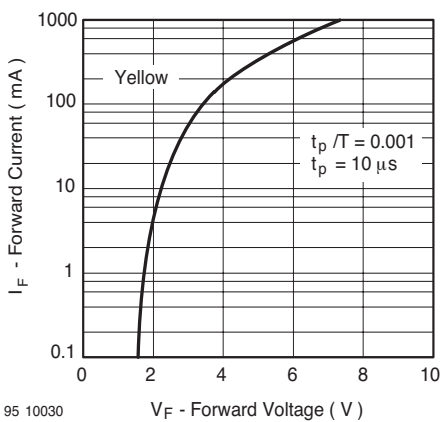


Figure 15. Forward Current vs. Forward Voltage

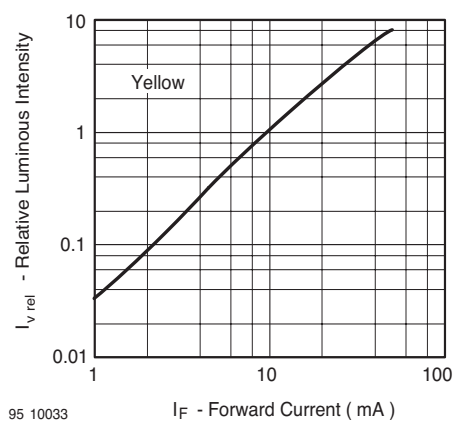


Figure 18. Relative Luminous Intensity vs. Forward Current



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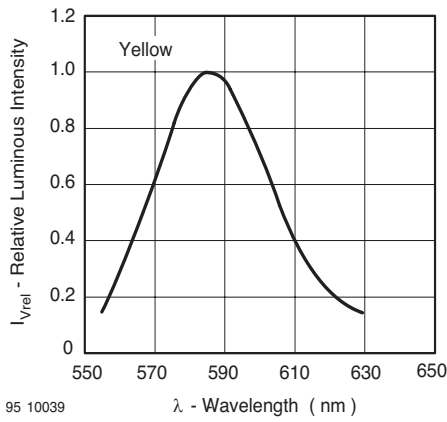


Figure 19. Relative Intensity vs. Wavelength

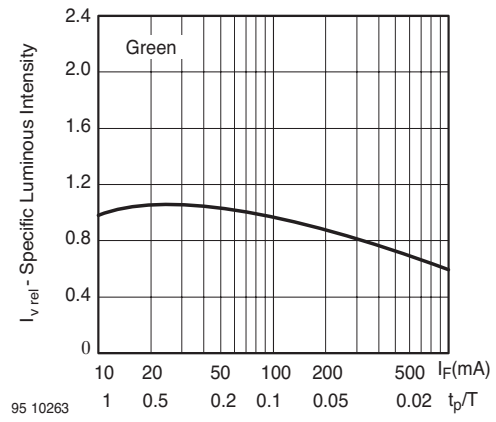


Figure 22. Specific Luminous Intensity vs. Forward Current

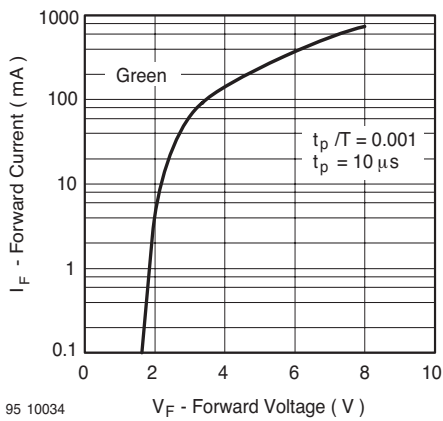


Figure 20. Forward Current vs. Forward Voltage

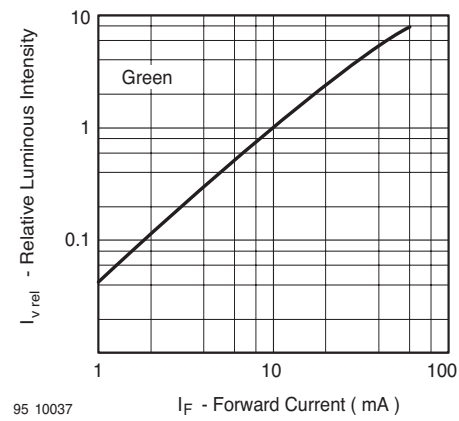


Figure 23. Relative Luminous Intensity vs. Forward Current

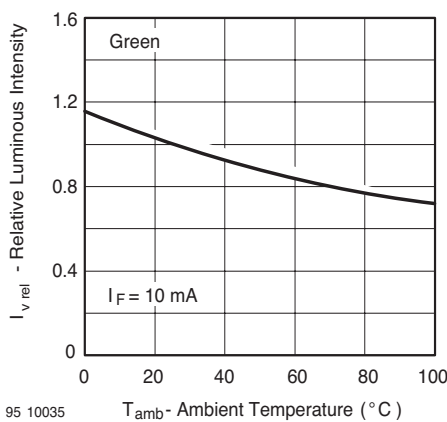


Figure 21. Rel. Luminous Intensity vs. Ambient Temperature

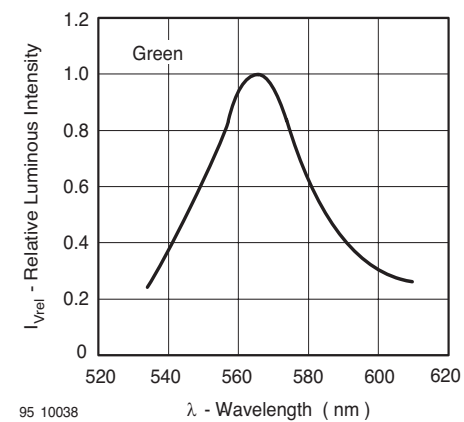


Figure 24. Relative Intensity vs. Wavelength

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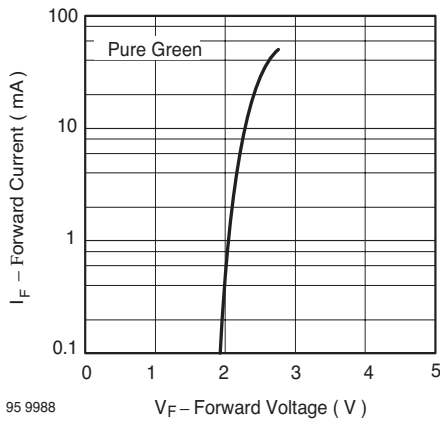


Figure 25. Forward Current vs. Forward Voltage

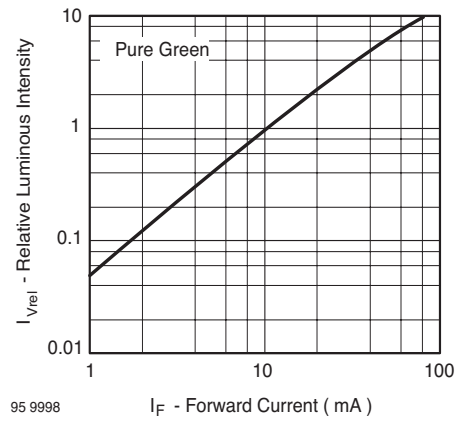


Figure 28. Relative Luminous Intensity vs. Forward Current

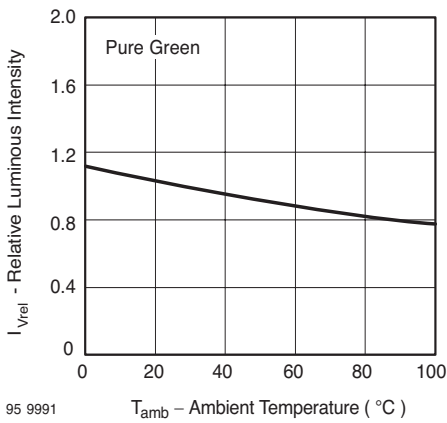


Figure 26. Rel. Luminous Intensity vs. Ambient Temperature

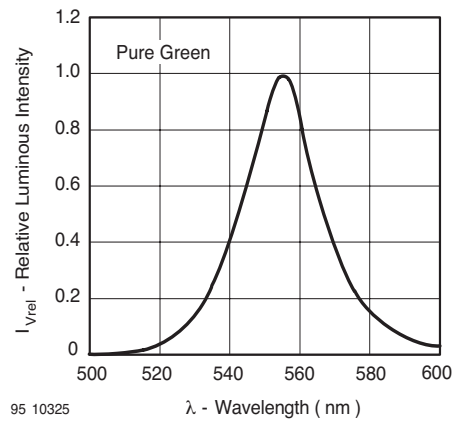


Figure 29. Relative Intensity vs. Wavelength

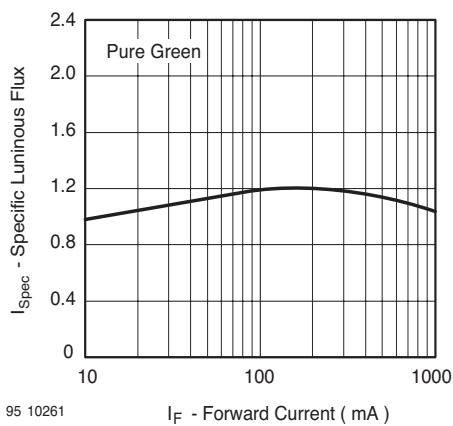


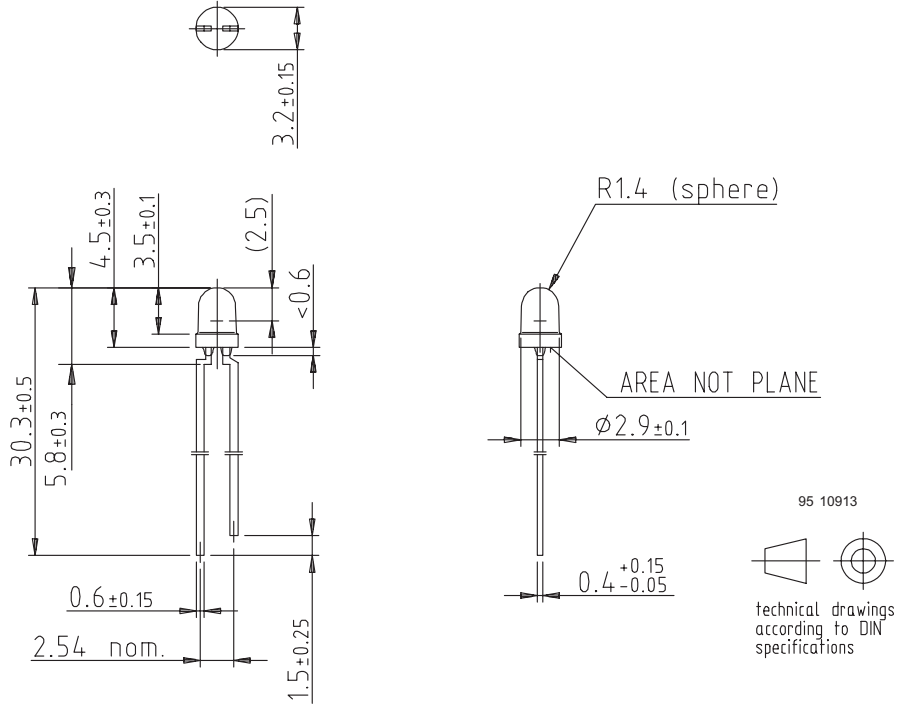
Figure 27. Specific Luminous Intensity vs. Forward Current



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Package Dimensions in mm





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Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany
Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423